

MOSFET

OptiMOS™ P3 Power-Transistor, -30 V

Features

- single P-Channel in S3O8
- Qualified according JEDEC¹⁾ for target applications
- 150 °C operating temperature
- V_{GS}=25 V, specially suited for notebook applications
- Pb-free; RoHS compliant
- applications: battery management, load switching
- Halogen-free according to IEC61249-2-21

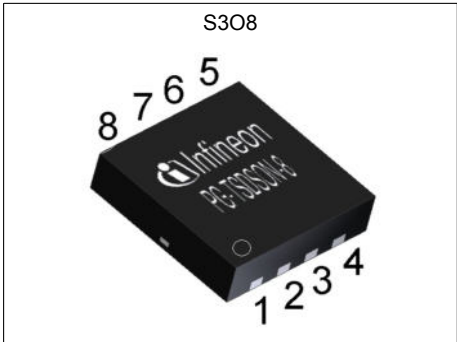
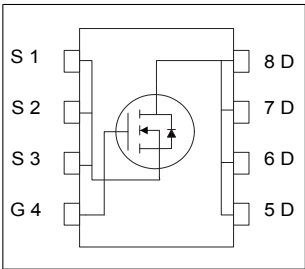


Table 1 Key Performance Parameters

Parameter	Value	Unit
V _{DS}	-30	V
R _{DS(on),max}	8.6	mΩ
I _D	-40	A



Type / Ordering Code	Package	Marking	Related Links
BSZ086P03NS3 G	PG-TSDSON-8	086P3N	-

¹⁾ J-STD20 and JESD22

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1 Maximum ratings

at $T_j=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	I_D	-	-	-40 -40 -13.5	A	$T_C=25\text{ °C}$ $T_C=70\text{ °C}$ $T_A=25\text{ °C}^{1)}$
Pulsed drain current	$I_{D,pulse}$	-	-	-160	A	$T_C=25\text{ °C}^{2)}$
Avalanche energy, single pulse	E_{AS}	-	-	105	mJ	$I_D=-20\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-25	-	25	V	-
Power dissipation	P_{tot}	-	-	69 2.1	-	$T_A=25\text{ °C}$ $T_A=25\text{ °C}^{1)}$
Operating and storage temperature	T_j , T_{stg}	-55	-	150	°C	IEC climatic category; DIN IEC 68-1: 55/150/56
ESD class	-	-	1C	-	-	(1kV-2kV), JESD22-A114 HBM
Soldering temperature	-	-	260	-	°C	-

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	1.8	K/W	-
Thermal resistance, junction - ambient, 6 cm ² cooling area ¹⁾	R_{thJA}	-	-	60	K/W	-

¹⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

²⁾ See Fig. 3 for more detailed information

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	-30	-	-	V	$V_{GS}=0\text{ V}$, $I_D=-250\text{ A}$
Gate threshold voltage	$V_{GS(th)}$	-3.1	-2.5	-1.9	V	$V_{DS}=V_{GS}$, $I_D=-105\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	-	-1 -10	μA	$V_{DS}=-30\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=-30\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	-	-100	nA	$V_{GS}=-25\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	6.5 8.7	8.6 13.4	m Ω	$V_{GS}=-10\text{ V}$, $I_D=-20\text{ A}$ $V_{GS}=-6\text{ V}$, $I_D=-20\text{ A}$
Gate resistance	R_G	-	2.2	-	Ω	-
Transconductance	g_{fs}	30	43	-	S	$ V_{DS} >2 I_D R_{DS(on)max}$, $I_D=-20\text{ A}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	3190	4785	pF	$V_{GS}=0\text{ V}$, $V_{DS}=-15\text{ V}$, $f=1\text{ MHz}$
Output capacitance	C_{oss}	-	1520	2280	pF	$V_{GS}=0\text{ V}$, $V_{DS}=-15\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance	C_{rss}	-	110	165	pF	$V_{GS}=0\text{ V}$, $V_{DS}=-15\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	16	24	ns	$V_{DD}=-15\text{ V}$, $V_{GS}=-10\text{ V}$, $I_D=-20\text{ A}$, $R_{G,ext}=6\text{ }\Omega$
Rise time	t_r	-	46	69	ns	$V_{DD}=-15\text{ V}$, $V_{GS}=-10\text{ V}$, $I_D=-20\text{ A}$, $R_{G,ext}=6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	35	53	ns	$V_{DD}=-15\text{ V}$, $V_{GS}=-10\text{ V}$, $I_D=-20\text{ A}$, $R_{G,ext}=6\text{ }\Omega$
Fall time	t_f	-	8	12	ns	$V_{DD}=-15\text{ V}$, $V_{GS}=-10\text{ V}$, $I_D=-20\text{ A}$, $R_{G,ext}=6\text{ }\Omega$

Table 6 Gate charge characteristics¹⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	16.1	21.4	nC	$V_{DD}=-15\text{ V}$, $I_D=-20\text{ A}$, $V_{GS}=0\text{ to }-10\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	5.0	6.7	nC	$V_{DD}=-15\text{ V}$, $I_D=-20\text{ A}$, $V_{GS}=0\text{ to }-10\text{ V}$
Gate to drain charge	Q_{gd}	-	7.4	11.1	nC	$V_{DD}=-15\text{ V}$, $I_D=-20\text{ A}$, $V_{GS}=0\text{ to }-10\text{ V}$
Switching charge	Q_{sw}	-	18.4	25.7	nC	$V_{DD}=-15\text{ V}$, $I_D=-20\text{ A}$, $V_{GS}=0\text{ to }-10\text{ V}$
Gate charge total	Q_g	-	43.2	57.5	nC	$V_{DD}=-15\text{ V}$, $I_D=-20\text{ A}$, $V_{GS}=0\text{ to }-10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	-4.5	-	V	$V_{DD}=-15\text{ V}$, $I_D=-20\text{ A}$, $V_{GS}=0\text{ to }-10\text{ V}$
Output charge	Q_{oss}	-	34.9	46.4	nC	$V_{DD}=-15\text{ V}$, $V_{GS}=0\text{ V}$

¹⁾ See Fig. 3 for more detailed information

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	-40	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	-160	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	-	-1.1	V	$V_{GS}=0\text{ V}$, $I_F=-40\text{ A}$, $T_j=25\text{ °C}$
Reverse recovery time	t_{rr}	-	39	-	ns	$V_R=15\text{ V}$, $I_F= I_S $, $di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}	-	34	-	nC	$V_R=15\text{ V}$, $I_F= I_S $, $di_F/dt=100\text{ A}/\mu\text{s}$

4 Electrical characteristics diagrams

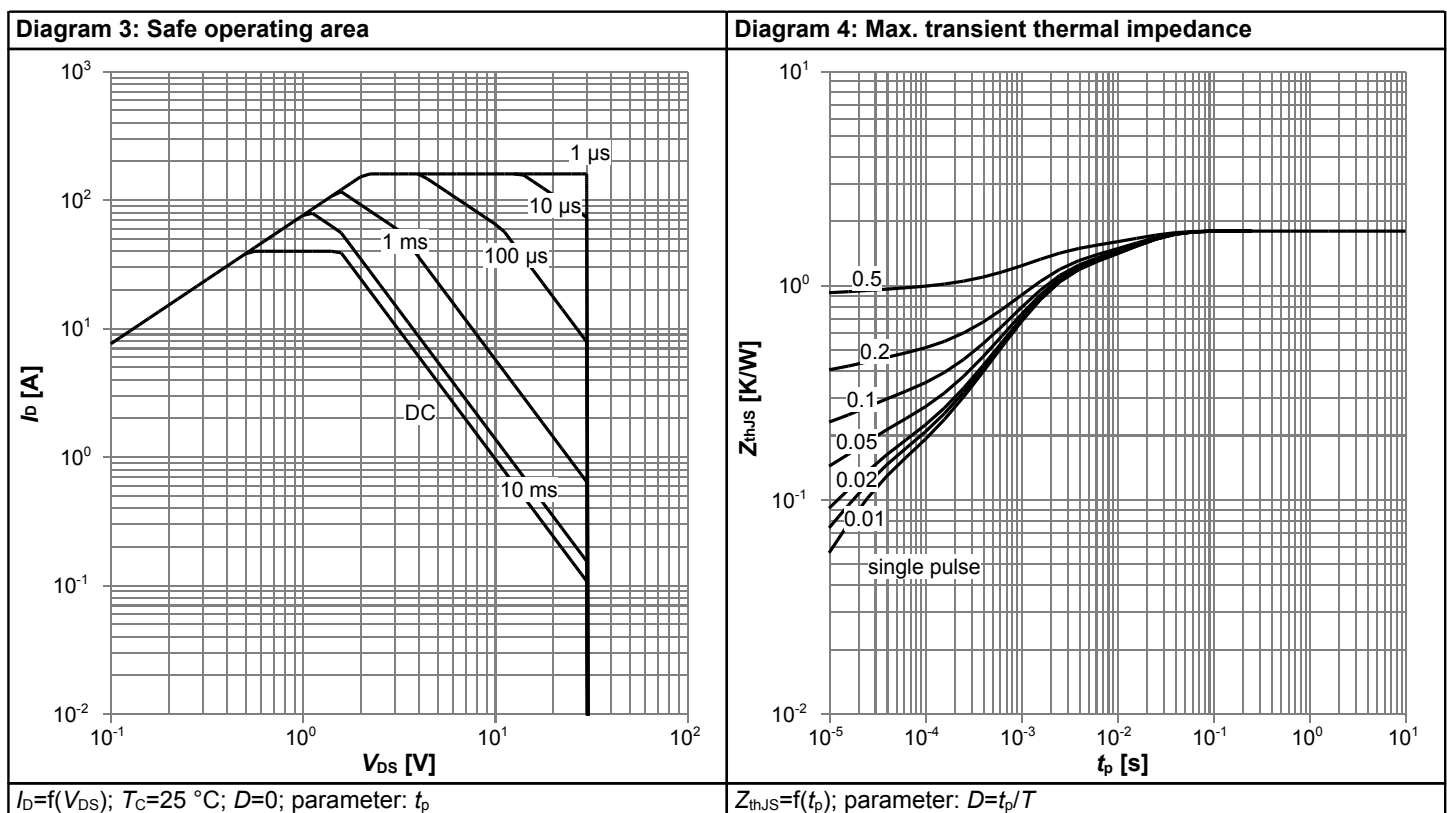
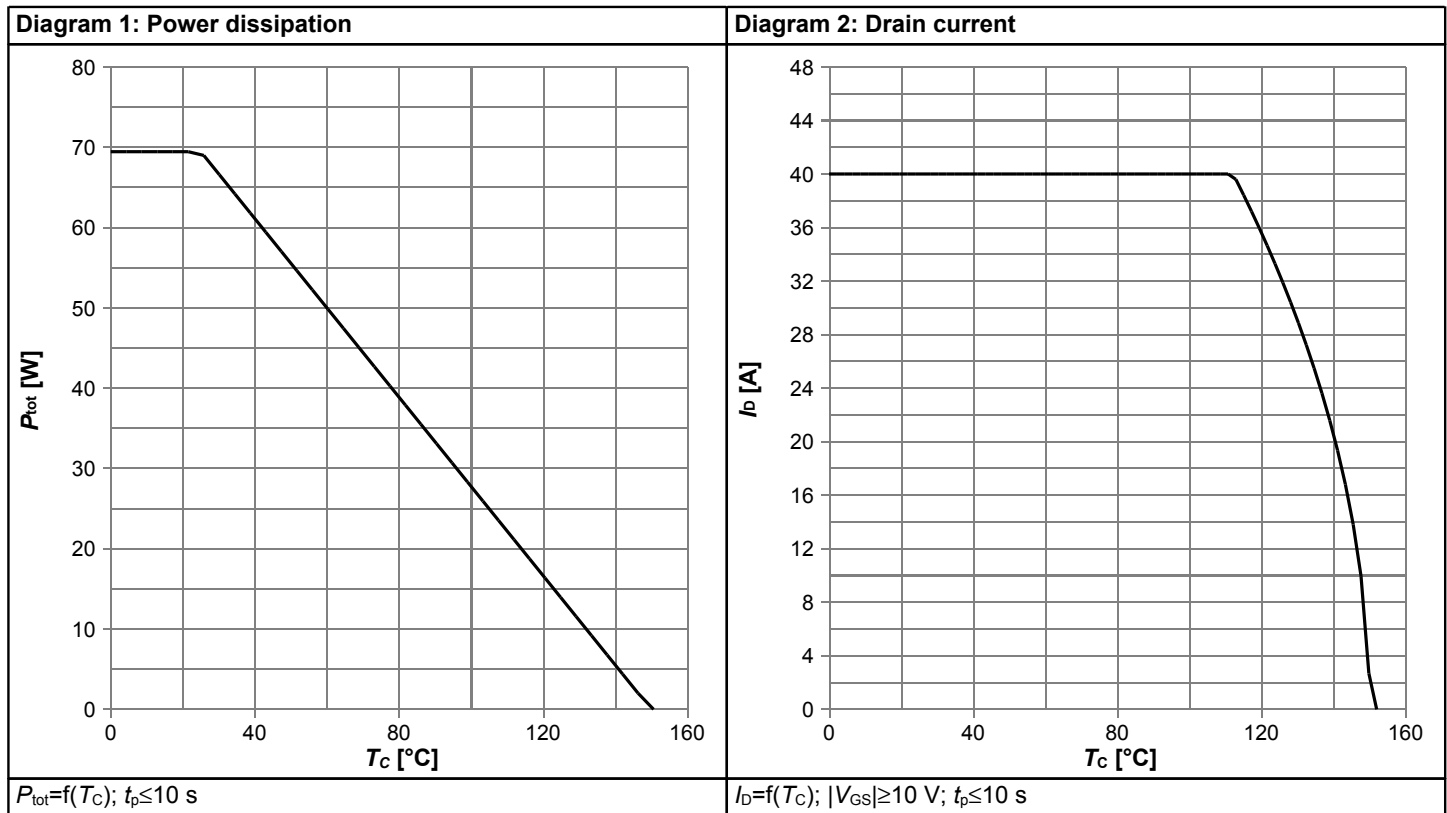
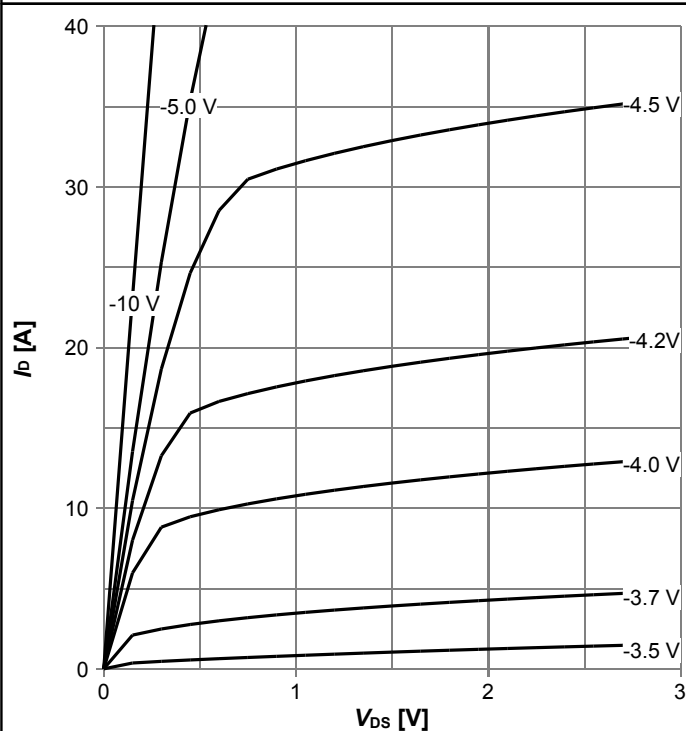
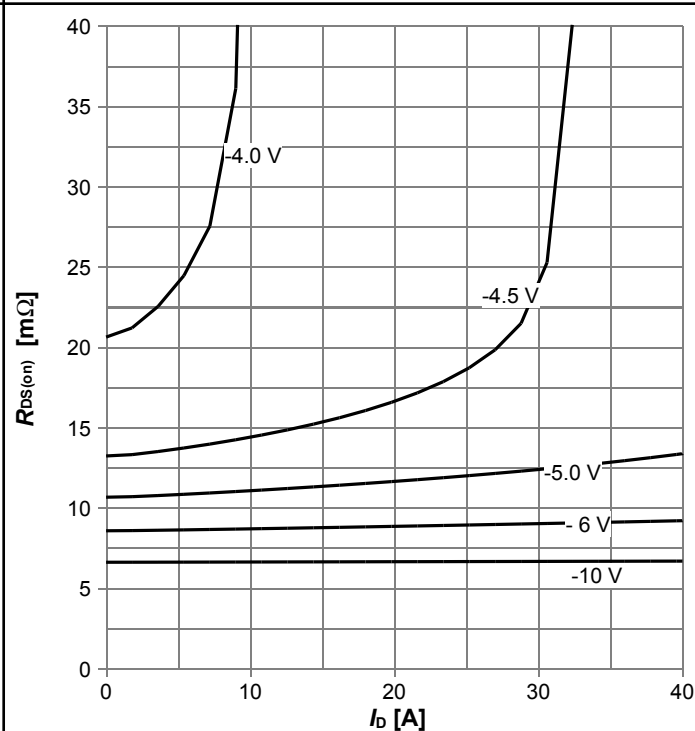


Diagram 5: Typ. output characteristics



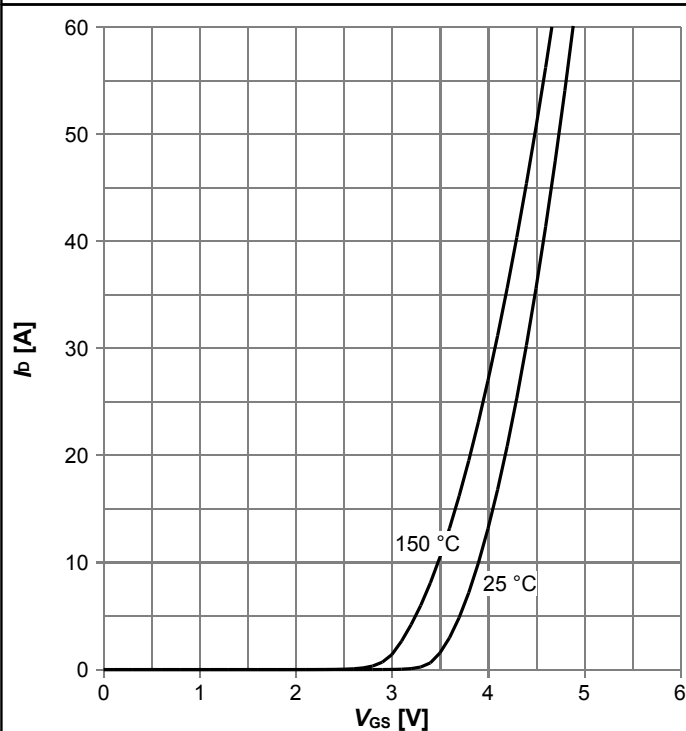
$I_D = f(V_{DS})$; $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



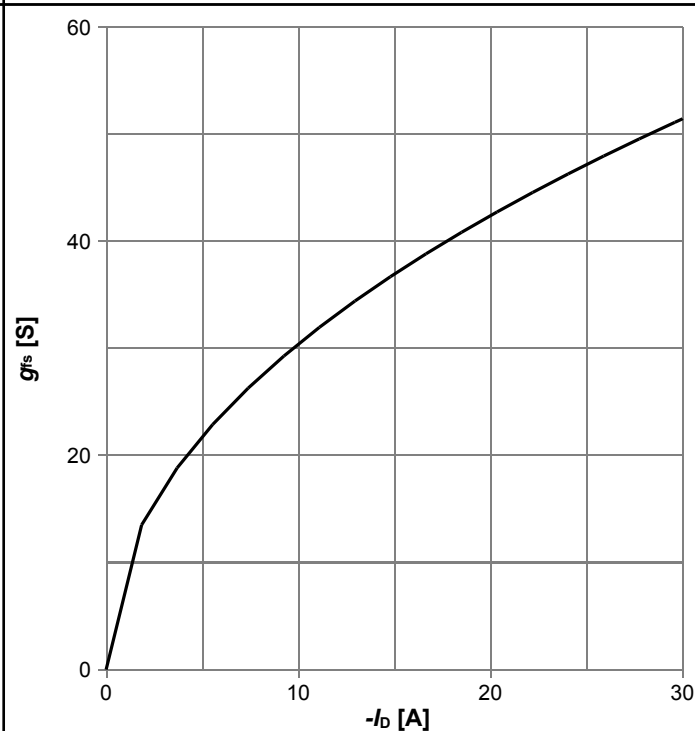
$R_{DS(on)} = f(I_D)$; $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



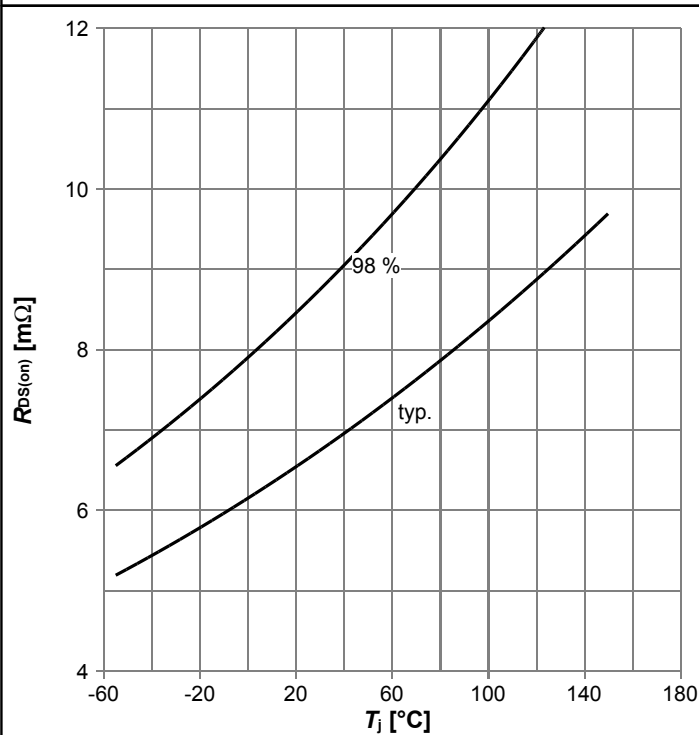
$I_D = f(V_{GS})$; $|V_{DS}| > 2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. forward transconductance



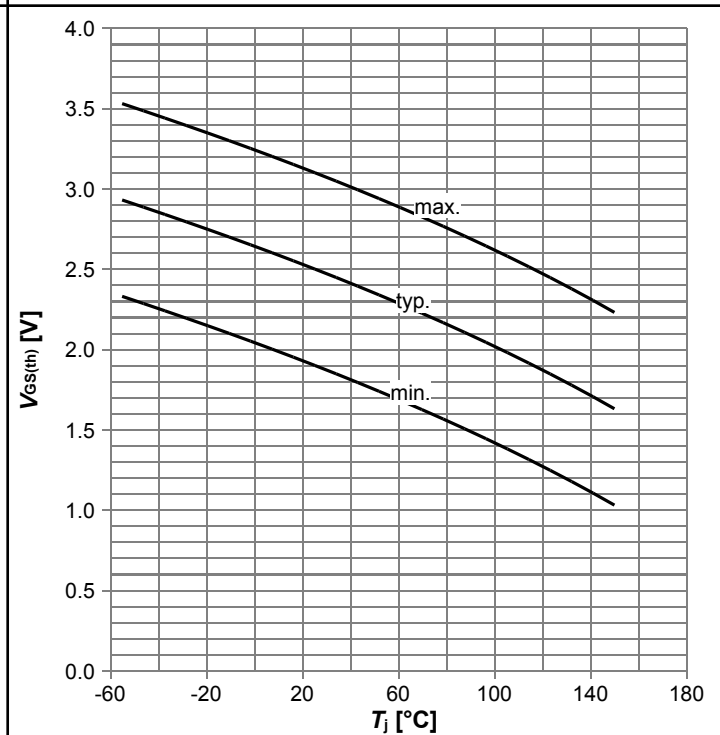
$g_{fs} = f(I_D)$; $T_j = 25^\circ\text{C}$

Diagram 9: Drain-source on-state resistance



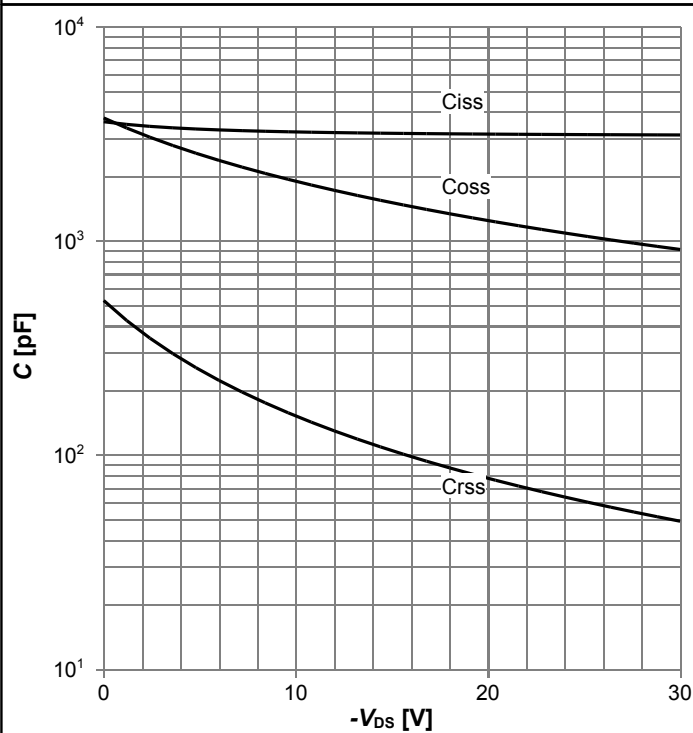
$R_{DS(on)} = f(T_j)$; $I_D = -20$ A; $V_{GS} = -10$ V

Diagram 10: Typ. gate threshold voltage



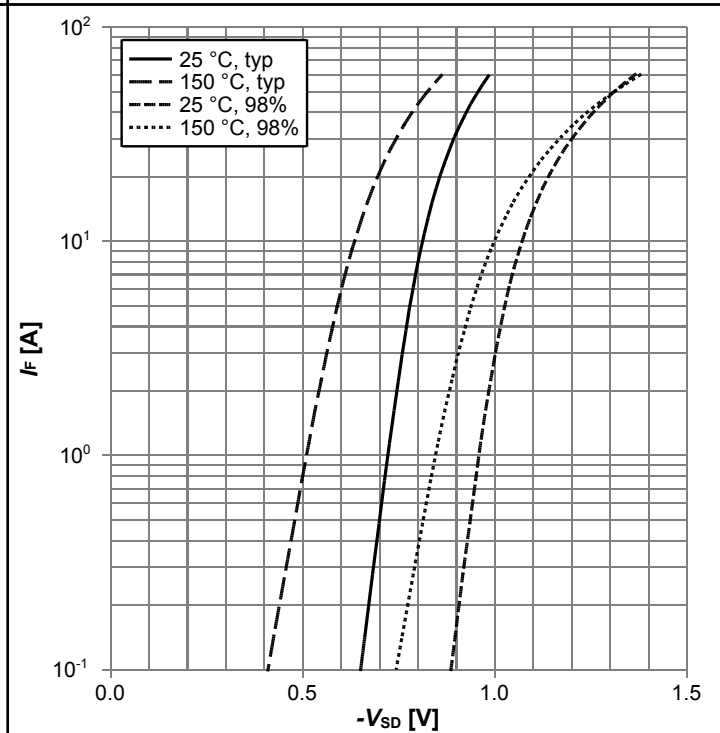
$V_{GS(th)} = f(T_j)$; $V_{GS} = V_{DS}$; $I_D = -105$ μ A

Diagram 11: Typ. capacitances



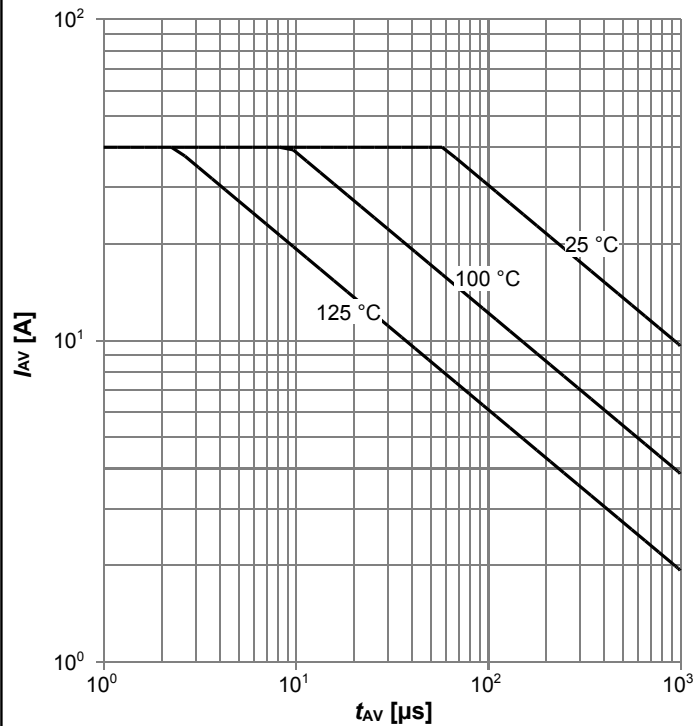
$C = f(V_{DS})$; $V_{GS} = 0$ V; $f = 1$ MHz

Diagram 12: Forward characteristics of reverse diode



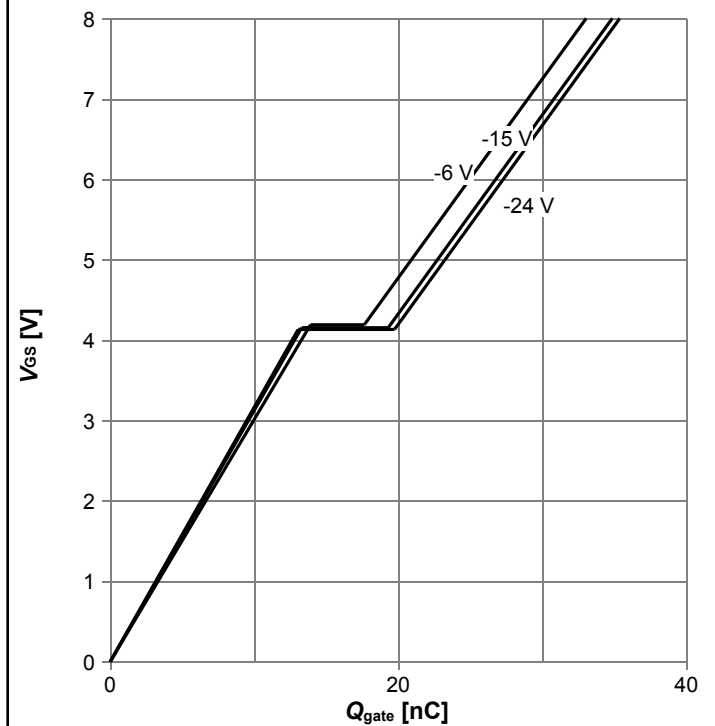
$I_F = f(V_{SD})$; parameter: T_j

Diagram 13: Avalanche characteristics



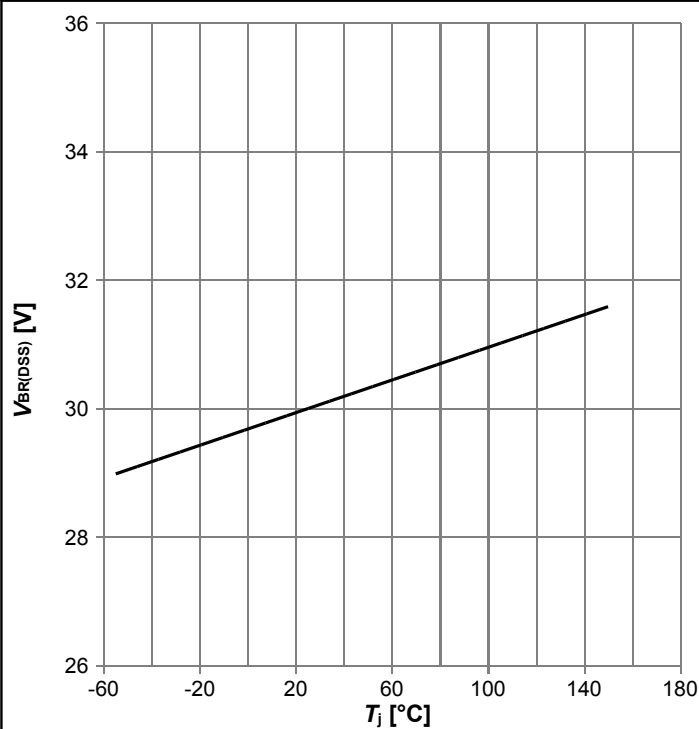
$I_{AS}=f(t_{AV})$; $R_{GS}=25\ \Omega$; parameter: $T_{j(start)}$

Diagram 14: Typ. gate charge



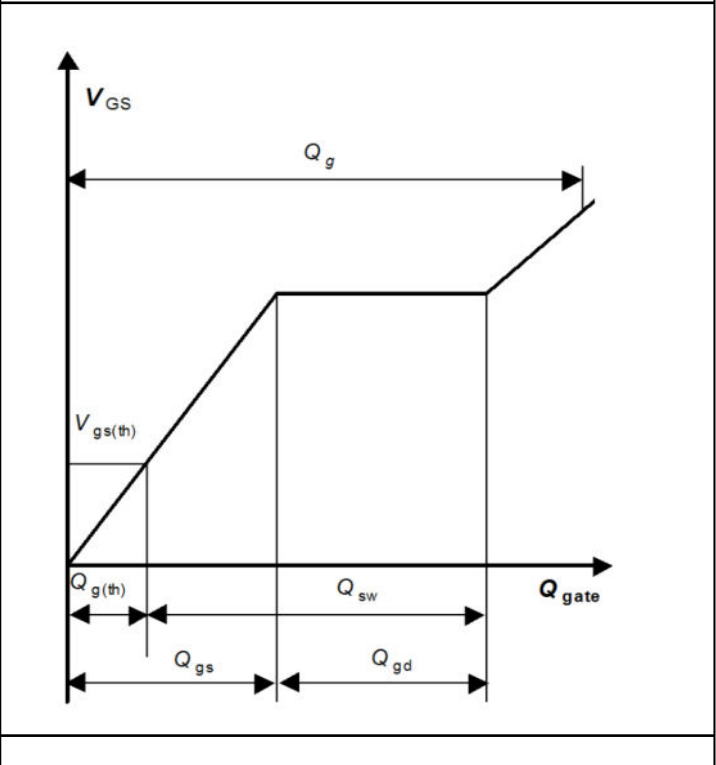
$V_{GS}=f(Q_{gate})$; $I_D=-20\text{ A}$ pulsed; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

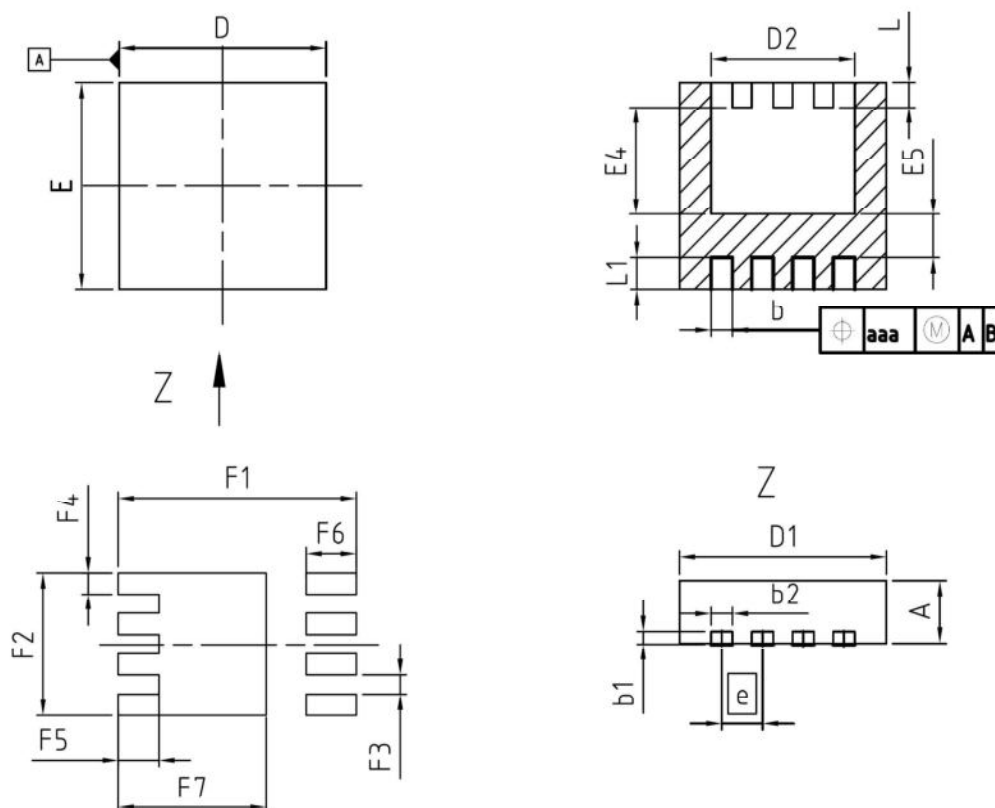


$V_{BR(DSS)}=f(T_J)$; $I_D=-250\ \mu\text{A}$

Diagram Gate charge waveforms



5 Package Outlines



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.10	0.035	0.043
b	0.24	0.44	0.009	0.017
b1	0.10	0.30	0.004	0.012
b2	0.20	0.44	0.008	0.017
D=D1	3.20	3.40	0.126	0.134
D2	2.15	2.45	0.085	0.096
E	3.20	3.40	0.126	0.134
E4	1.60	1.81	0.063	0.071
E5	0.59	0.86	0.023	0.034
e	0.65		0.026	
N	8		8	
L	0.30	0.56	0.012	0.022
L1	0.33	0.60	0.013	0.024
aaa	0.25		0.010	
F1	3.80		0.150	
F2	2.29		0.090	
F3	0.31		0.012	
F4	0.34		0.013	
F5	0.65		0.026	
F6	0.80		0.031	
F7	2.36		0.093	

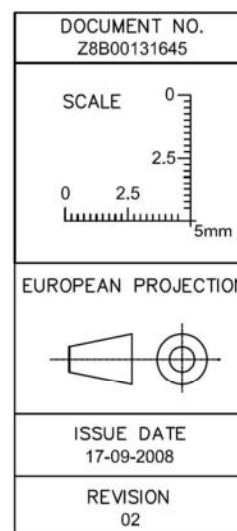


Figure 1 Outline PG-TSDSON-8, dimensions in mm/inches

Revision History

BSZ086P03NS3 G

Revision: 2019-12-03, Rev. 2.4

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.4	2019-12-03	Update SOA Diagram

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